
2SC3336

Silicon NPN Triple Diffused

HITACHI

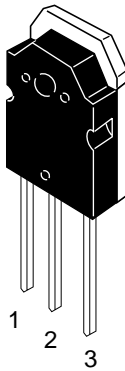
ADE-208-891 (Z)
1st. Edition
Sep. 2000

Application

High voltage, high speed and high power switching

Outline

TO-3P



1. Base
2. Collector
(Flange)
3. Emitter

Absolute Maximum Ratings (Ta = 25°C)

Item	Symbol	Ratings	Unit
Collector to base voltage	V_{CBO}	500	V
Collector to emitter voltage	V_{CEO}	400	V
Emitter to base voltage	V_{EBO}	10	V
Collector current	I_C	15	A
Collector peak current	$I_{C(peak)}$	25	A
Base current	I_B	7.5	A
Collector power dissipation	P_C^{*1}	100	W
Junction temperature	T_j	150	°C
Storage temperature	T_{stg}	-55 to +150	°C

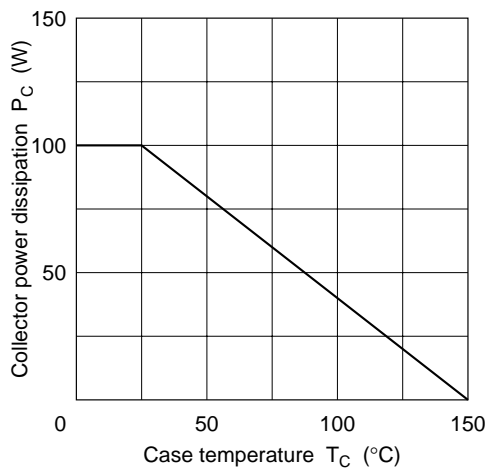
Note: 1. Value at $T_C = 25^\circ\text{C}$

Electrical Characteristics (Ta = 25°C)

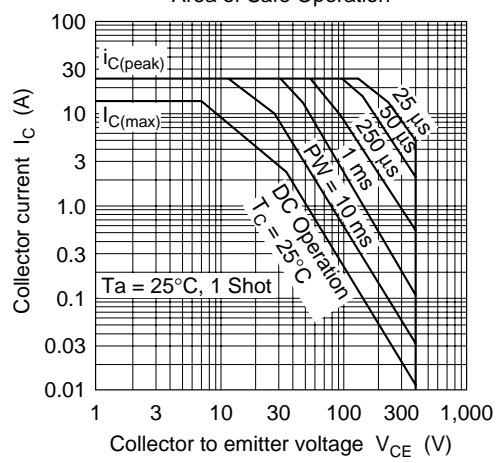
Item	Symbol	Min	Typ	Max	Unit	Test conditions
Collector to emitter sustain voltage	$V_{CEO(sus)}$	400	—	—	V	$I_C = 0.2\text{ A}$, $R_{BE} = \infty$, $L = 100\text{ mH}$
	$V_{CEX(sus)}$	400	—	—	V	$I_C = 15\text{ A}$, $I_{B1} = 3.0\text{ A}$, $I_{B2} = -1\text{ A}$, $V_{BE} = -5.0\text{ V}$, $L = 180\text{ }\mu\text{H}$, Clamped
Emitter to base breakdown voltage	$V_{(BR)EBO}$	10	—	—	V	$I_E = 10\text{ mA}$, $I_C = 0$
Collector cutoff current	I_{CBO}	—	—	50	μA	$V_{CB} = 400\text{ V}$, $I_E = 0$
	I_{CEO}	—	—	50	μA	$V_{CE} = 350\text{ V}$, $R_{BE} = \infty$
DC current transfer ratio	h_{FE1}	12	—	—		$V_{CE} = 5.0\text{ V}$, $I_C = 7.5\text{ A}^{*1}$
	h_{FE2}	5	—	—		$V_{CE} = 5.0\text{ V}$, $I_C = 15\text{ A}^{*1}$
Collector to emitter saturation voltage	$V_{CE(sat)}$	—	—	1.0	V	$I_C = 7.5\text{ A}$, $I_B = 1.5\text{ A}^{*1}$
Base to emitter saturation voltage	$V_{BE(sat)}$	—	—	1.5	V	
Turn on time	t_{on}	—	—	0.5	μs	$I_C = 15\text{ A}$, $I_{B1} = -I_{B2} = 3.0\text{ A}$
Storage time	t_{stg}	—	—	1.5	μs	$V_{CC} \cong 150\text{ V}$
Fall time	t_f	—	0.3	0.5	μs	

Note: 1. Pulse test

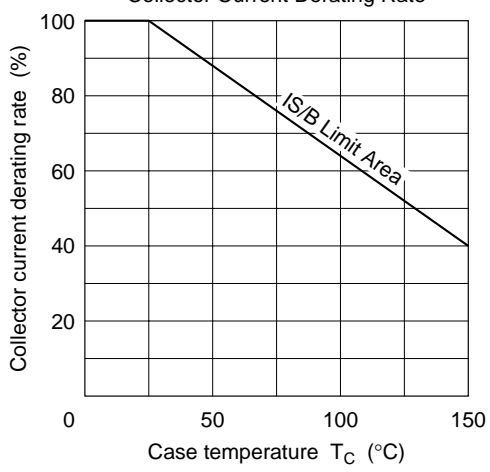
Maximum Collector Dissipation Curve



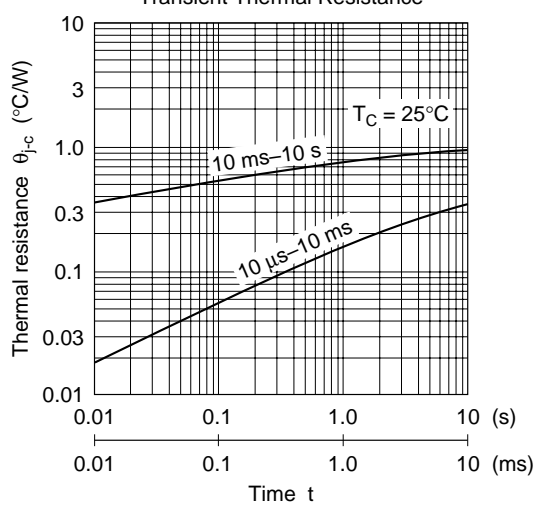
Area of Safe Operation

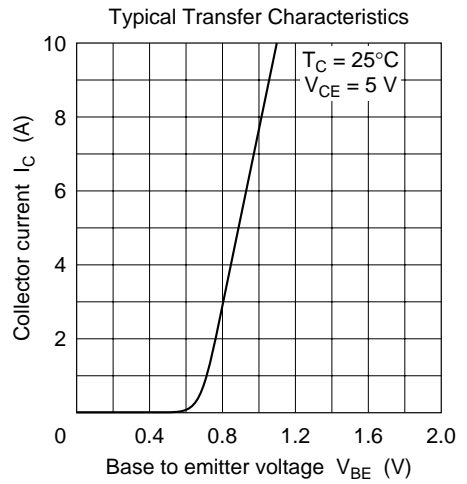
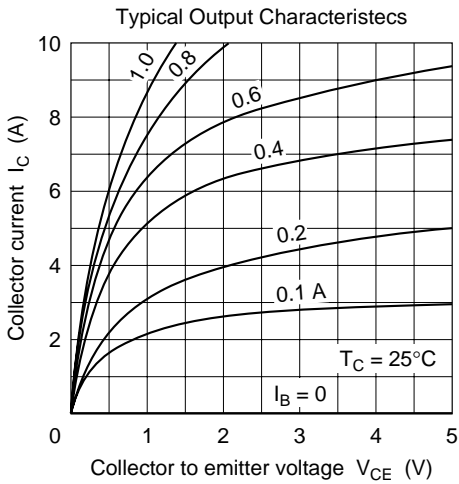
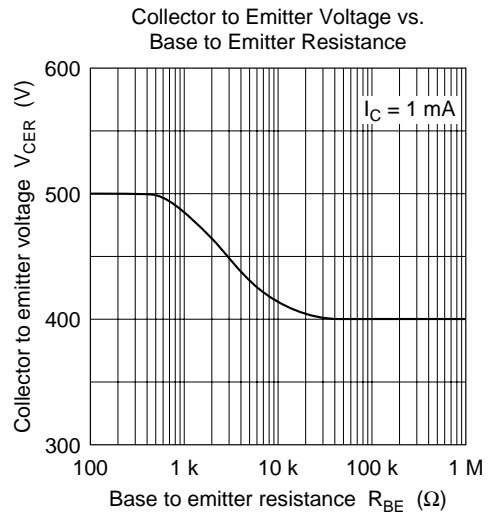
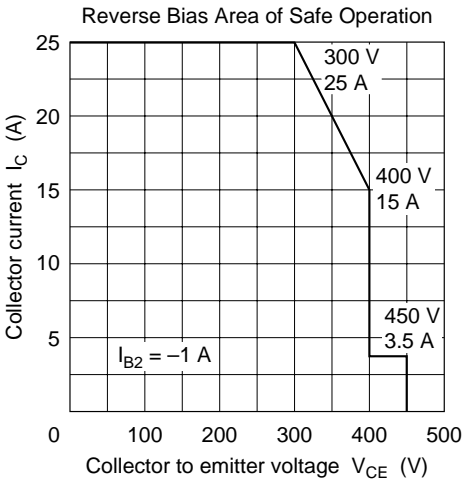


Collector Current Derating Rate

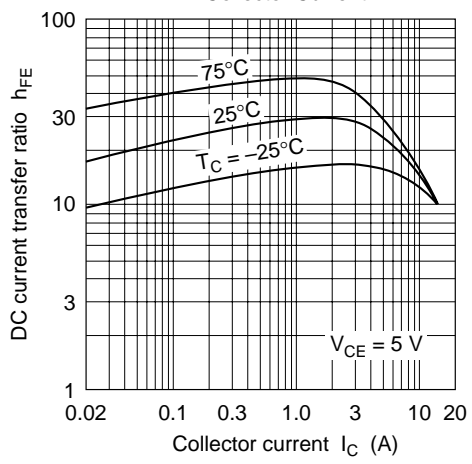


Transient Thermal Resistance

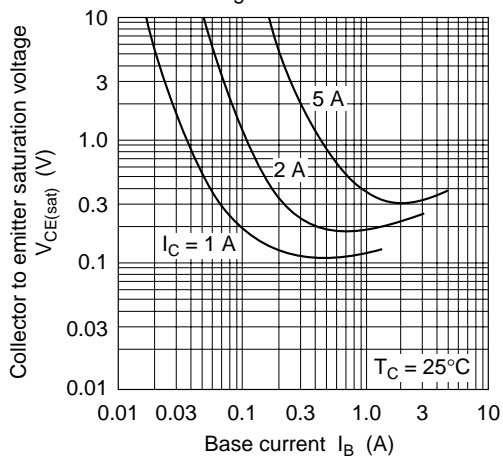




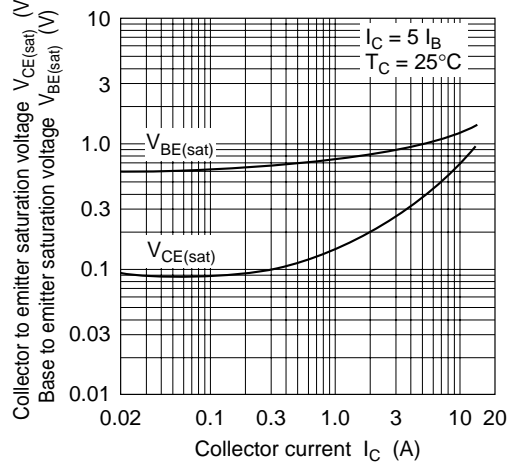
DC Current Transfer Ratio vs.
Collector Current



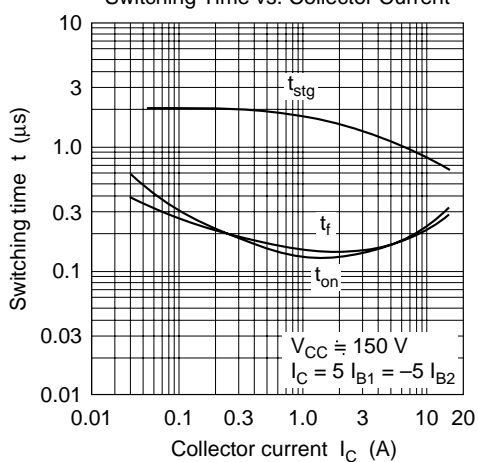
Collector to Emitter Saturation
Voltage vs. Base Current

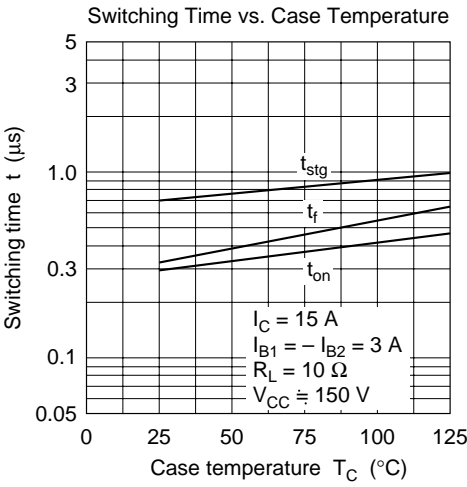


Saturation Voltage vs.
Collector Current



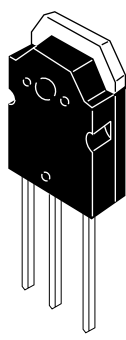
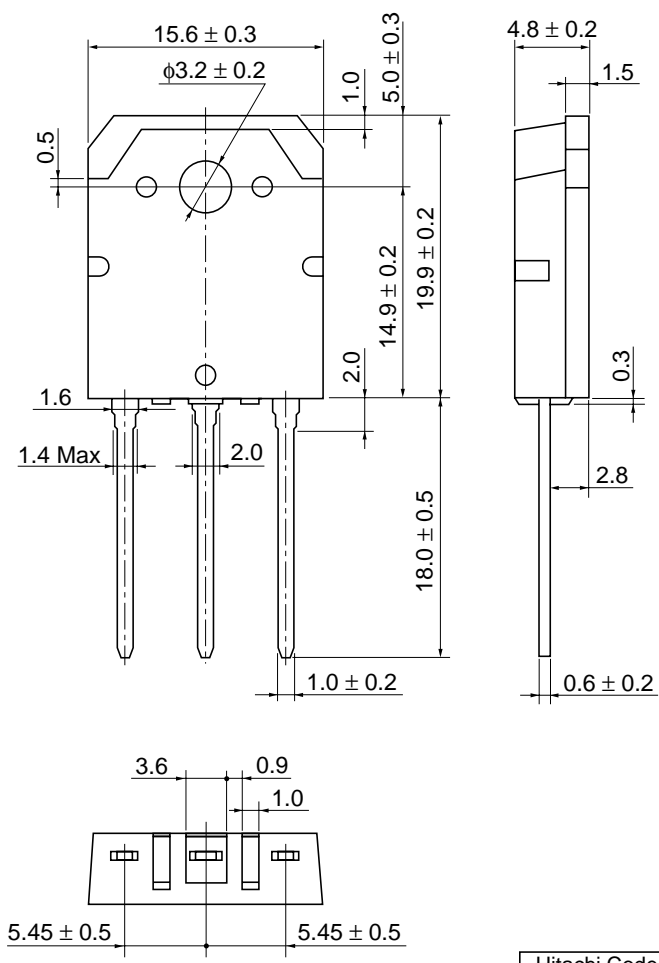
Switching Time vs. Collector Current





Package Dimensions

Unit: mm



Hitachi Code	TO-3P
JEDEC	—
EIAJ	Conforms
Mass (reference value)	5.0 g

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Hitachi, Ltd.

Semiconductor & Integrated Circuits.
Nippon Bldg., 2-6-2, Ohte-machi, Chiyoda-ku, Tokyo 100-0004, Japan
Tel: Tokyo (03) 3270-2111 Fax: (03) 3270-5109

URL	North America	: http://semiconductor.hitachi.com/
	Europe	: http://www.hitachi-eu.com/hel/ecg
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For further information write to:

Hitachi Semiconductor
(America) Inc.
179 East Tasman Drive,
San Jose, CA 95134
Tel: <1> (408) 433-1990
Fax: <1> (408) 433-0223

Hitachi Europe GmbH
Electronic Components Group
Dornacher Straße 3
D-85622 Feldkirchen, Munich
Germany
Tel: <49> (89) 9 9180-0
Fax: <49> (89) 9 29 30 00

Hitachi Europe Ltd.
Electronic Components Group.
Whitebrook Park
Lower Cookham Road
Maidenhead
Berkshire SL6 8YA, United Kingdom
Tel: <44> (1628) 585000
Fax: <44> (1628) 585160

Hitachi Asia Ltd.
Hitachi Tower
16 Collyer Quay #20-00,
Singapore 049318
Tel: <65>-538-6533/538-8577
Fax: <65>-538-6933/538-3877
URL: <http://www.hitachi.com.sg>

Hitachi Asia Ltd.
(Taipei Branch Office)
4/F, No. 167, Tun Hwa North Road,
Hung-Kuo Building,
Taipei (105), Taiwan
Tel: <886>-(2)-2718-3666
Fax: <886>-(2)-2718-8180
Telex: 23222 HAS-TP
URL: <http://www.hitachi.com.tw>

Hitachi Asia (Hong Kong) Ltd.
Group III (Electronic Components)
7/F., North Tower,
World Finance Centre,
Harbour City, Canton Road
Tsim Sha Tsui, Kowloon,
Hong Kong
Tel: <852>-(2)-735-9218
Fax: <852>-(2)-730-0281
URL: <http://www.hitachi.com.hk>

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